

Designed for broadband high power applications, this amplifier utilizes linear Silicon RF Power MOSFET devices that provide high gain, wide dynamic range and good linearity. Exceptional performance, long term reliability and high efficiency are achieved by employing advanced broadband RF matching networks and combining techniques, EMI/RFI filters, machined housings and all qualified components. Each unit undergoes extensive burn-in prior to final test and inspection.

ELECTRICAL SPECIFICATIONS		
Characteristics	Rating	Limit
Frequency Response	20 – 500 MHz	Min
Power Output CW	50 Watts	Min
Power Output @ 1 dB comp.	30 Watts	Min
Third Order Intercept Point	+55 dBm	Typ
Small Signal Gain	48 dB	Min
Small Signal Gain Flatness	±1.5 dB	Max
Input Overdrive	+10 dBm	Max
Input/Output VSWR @ 50 ohm	2:1	Max
Harmonics @ 1 dB compression	-20 dBc	Typ
Noise Figure	10 dB	Max
Spurious Signals	-60 dBc	Max
Supply Voltage	28 VDC	Nom
Current Consumption	8.0 Amp	Max

ENVIRONMENTAL CHARACTERISTICS

Operating Temperature: 0°C to +50°C
 Non-operating Temperature: -40°C to +85°C
 Humidity: 95% relative without condensation
 Altitude: 10,000 feet
 Shock and Vibration: Normal truck transport

CIRCUIT PROTECTIONS

Infinite Load VSWR
 RF Input Overdrive
 Thermal Overload

MECHANICAL SPECIFICATIONS

Dimensions	6.4"x3.4"x1.1"	Max
Weight	1.0 lb.	Max
RF Connectors	SMA female	
Cooling	External Heatsink	

